TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM16G48,USM16G48,SM16J48,USM16J48 SM16G48A,USM16G48A,SM16J48A,USM16J48A

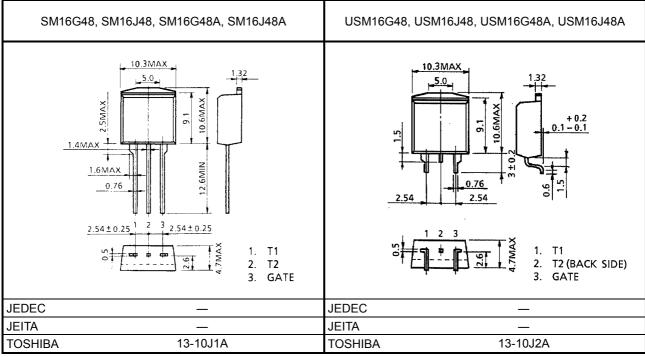
AC POWER CONTROL APPLICATIONS

Repetitive Peak Off-State Voltage :VDRM=400, 600V
 R.M.S On-State Current :IT (RMS)=16A

• Gate Trigger Current :I_{GT}=30mA Max.

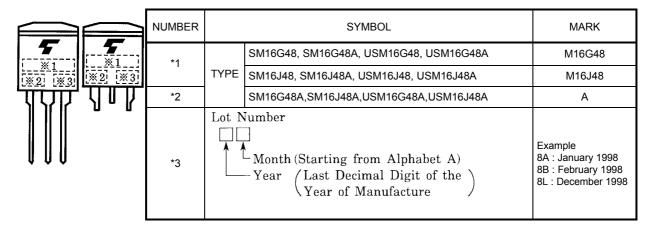
:IGT=20mA Max. ("A"Type)

Unit in mm



Weight: 1.7g

MARKING



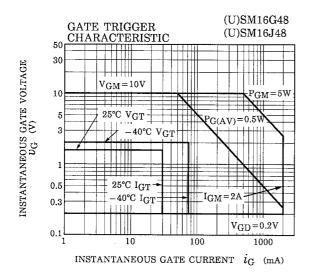
MAXIMUM RATINGS (Ta=25°C)

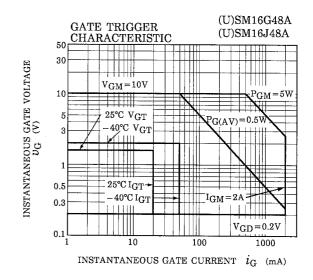
CHARACT	ERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage	(U)SM12G48 (U)SM12G48A	V_{DRM}	400	>	
	(U)SM12J48 (U)SM12J48A	¥ DRM	600		
R.M.S On-State Cur	rent	I _{T (RMS)}	16	А	
Peak One Cycle Sur	ge On-State	l -	150 (50Hz)	A	
Current (Non-Repeti	tive)	ITSM	165 (60Hz)		
I ² t Limit Value		I ² t	112.5	A ² s	
Critical Rate of Rise Current	of On-State (Note 1)	di /dt	50	A / μs	
Peak Gate Power Di	ssipation	P_{GM}	5	W	
Average Gate Powe	r Dissipation	P _{G (AV)}	0.5	W	
Peak Forward Gate	Voltage	V_{GM}	10	V	
Peak Forward Gate	Current	I _{GM}	2	Α	
Junction Temperatu	re	Tj	-40~125	°C	
Storage Temperatur	e Range	T _{stg}	-40~125	°C	

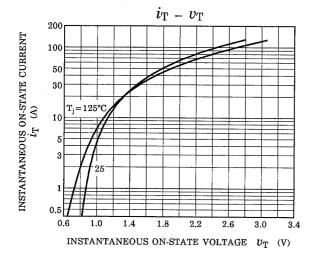
Note 1 : $V_{DRM}=0.5\times Rated$ $I_{TM}\leq 25A$ $t_{gw}\geq 10\mu s$ $t_{gr}\leq 250ns$ $i_{gp}=I_{GT}\times 2.0$

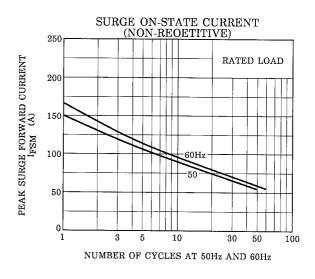
ELECTRICAL CHARACTERISTICS (Ta=25°C)

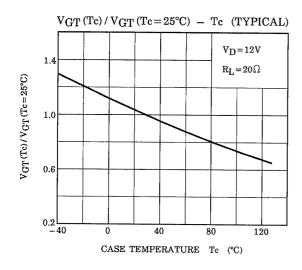
CHARACTERISTIC			SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT	
Repetitive Peak Off-State Current			I _{DRM}	V _{DRM} =Rated		_	_	20	μА	
I			V _D =12V	T2 (+), Gate (+)	_	_	1.5	V		
				T2 (+) , Gate (-)	_	_	1.5			
		III	V _{GT}	R _L =20Ω	T2 (-) , Gate (-)	_	_	1.5	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
				T2 (-) , Gate (+)	_	_	_			
Gate Trigger Current (U		(U)SM16G48 (U)SM16J48			V _D =12V	T2 (+), Gate (+)	_	_	30	
	(U)SN					T2 (+), Gate (-)	_	_	30	
	(U)SN					T2 (-) , Gate (-)	_	_	30	
						T2 (-) , Gate (+)	_	50	_	
		(U)SM16G48A (U)SM16J48A	I	IGT	R _L =20Ω	T2 (+), Gate (+)	_	_	20	mA
	(U)SN		П			T2 (+), Gate (-)	_	_	20	
	(U)SN		III			T2 (-) , Gate (-)	_	_	20	
						T2 (-) , Gate (+)	_	_	_	
Peak On-State Voltage		V_{TM}	I _{TM} =17A		_	_	1.5	_		
Gate Non-Trigger Voltage			V _{GD}	V _D =Rated, Tc=125°C		0.2	_	_	V	
Holding Current			lΗ	V _D =12V, I _{TM} =1A		_	_	50	mA	
Thermal Resistance			R _{th (j-c)}	Junction to Case, AC		_	_	2.0	°C/W	
Critical Rate of Rise of Off-State Voltage	(U)SM16G48 (U)SM16J48		dv / dt	V _{DRM} =Rated, T _i =125°C		_	300	_	· V / μs	
	e	(U)SM16G48A (U)SM16J48A		uv / ut	Exponential Rise		_	200	_	ν / μδ
Critical Rate of Rise of Off-State Voltage at Commutation	(U)SM16G48 (U)SM16J48		(dv. / dt) =	V _{DRM} =400V, T _i =125°C		10	_	_	- V / μs	
	(U)SM16G (U)SM16J4		(dv / dt) c	(dv / dt) c $(di / dt) c = -8.7 Å / ms$		4	_	_	¬ ν / μs	

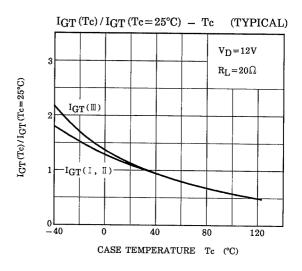


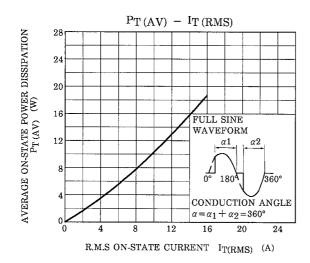


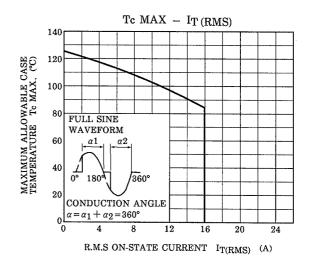


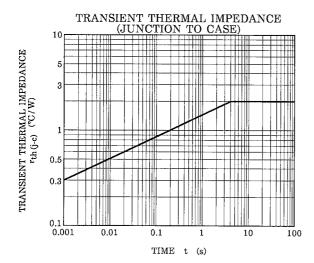


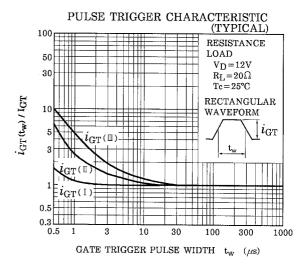


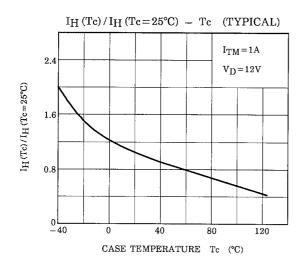












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